

Part Number

Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm
	2.0	Primary Flat Orientation	{110} +/- 1 degree
	3.0	Primary Flat Length	32.50 +/- 2.50 mm
	4.0	Secondary Flat Orientation	none/semi standard
	5.0	Secondary Flat Length	none / 18.5mm +/-2.5mm
	6.0	Overall Thickness	401.00 +/- 6.00 µm
	7.0	Total Thickness Variation (TTV)	<5.00µm
	8.0	Bow	<60.00µm
	9.0	Warp	<60.00µm
	10.0	Edge Chips	0
	11.0	Edge Exclusion	5mm
HandleSilicon	12.0	Handle Growth Method	CZ
	13.0	Handle Orientation	{100} +/- 1 degree
	14.0	Handle Thickness	390.00 +/- 5.00 µm
	15.0	Handle Doping Type	P
	16.0	Handle Dopant	Any
	17.0	Handle Resistivity	0.01 ~ 0.02 Ohm-cm
	18.0	Backside Finish	Polished with oxide and lasermark.
BuriedOxide	19.0	Oxide Type	Thermal
	20.0	Oxide Thickness	10,000.00 +/- 1,000.00 Å
	21.0	Oxide formed on	Handle and / or device Wafer
DeviceSilicon	22.0	Device Growth Method	CZ
	23.0	Device Orientation	{100} +/- 1 degree
	24.0	Nominal Thickness	10.00 +/- 1.00 µm
	25.0	Distance to device silicon edge from wafer edge	<= 2mm
	26.0	Device Doping Type	P
	27.0	Device Dopant	Boron
	28.0	Device Resistivity	0.001 ~ 0.002 Ohm-cm
	29.0	Voids	none
	30.0	Scratches	0
	31.0	Haze	none

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information